

MA3XD15

Silicon epitaxial planar type

For rectification

For protection against reverse current

■ Features

- Mini type 3-pin package
- Low V_F or Low I_R type: $V_F < 0.45$ V, $I_R < 100$ μ A
- Allowing to rectify under ($I_{F(AV)} = 1$ A) condition

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	25	V
Non-repetitive peak forward surge current* ¹	I_{FSM}	3	A
Average forward current* ²	$I_{F(AV)}$	1.0	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

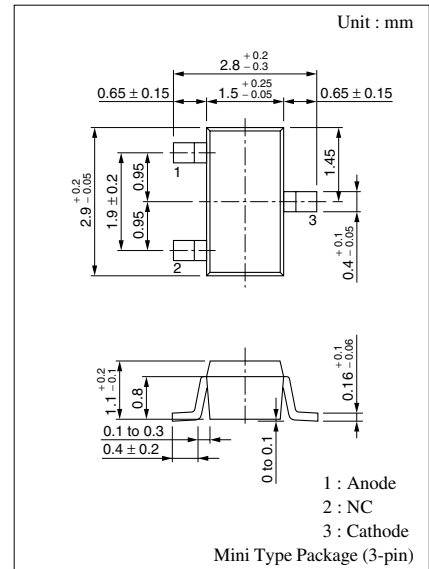
Note) *1: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

*2: With a alumina PC board

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 20$ V			100	μ A
Forward voltage (DC)	V_F	$I_F = 1.0$ A			0.45	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		120		pF

Note) Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.



Marking Symbol: M5N

Internal Connection

